

Customer No.: 31561
Docket No.: 14150-US-PA
Application No.: 10/711,864

AMENDMENTS

In The Claims

Claim 1. (currently amended) A method for fabricating poly-crystal indium tin oxide (ITO) film, the method comprising:

forming an amorphous ITO film on a substrate; and

performing ~~[[a]]~~one rapid thermal annealing (RTA) process, to transform the amorphous ITO film into a poly-crystal ITO film.

Claim 2. (original) The method of claim 1, wherein the step of forming the amorphous ITO film includes sputtering, physical vapor deposition, or chemical vapor deposition.

Claim 3. (original) The method of claim 1, wherein a thickness of the amorphous ITO film is 400 – 1500 angstroms.

Claim 4. (original) The method of claim 1, wherein the RTA process is operated under 400°C – 700°C for 0.5 – 6 minutes.

Claim 5. (original) The method of claim 1, wherein the substrate includes glass substrate, silicon substrate, or plastic substrate.

Claim 6. (original) The method of claim 1, wherein substrate includes rigid substrate or flexible substrate.

Claim 7. (currently amended) A method for fabricating poly-crystal indium tin oxide (ITO) electrode, suitable for use to form electrodes in a thin film transistor array, a color filter, a light emitting diode, or an organic electro-luminescence display, the method comprising:

Customer No.: 31561
Docket No.: 14150-US-PA
Application No.: 10/711,864

forming an amorphous ITO film on a substrate;
patterning the amorphous ITO film, to form a plurality of amorphous ITO electrodes on the substrate; and
performing ~~[[a]]~~one rapid thermal annealing (RTA) process, to transform the amorphous ITO electrodes into a plurality of poly-crystal ITO electrodes.

Claim 8. (original) The method of claim 7, wherein the step of forming the amorphous ITO film includes sputtering, physical vapor deposition, or chemical vapor deposition.

Claim 9. (original) The method of claim 7, wherein a thickness of the amorphous ITO electrode is 400 – 1500 angstroms.

Claim 10. (original) The method of claim 7, wherein the step of patterning the amorphous ITO film includes:

forming a patterned photoresist layer on the amorphous ITO film;
removing a portion of the amorphous ITO film by using the photoresist layer as the pattern as a mask, so as to form the amorphous ITO electrodes on the substrate; and
removing the photoresist layer.

Claim 11. (original) The method of claim 10, wherein the portion of the amorphous ITO film is removed by oxalic acid.

Claim 12. (original) The method of claim 7, wherein the RTA process is operated under 400°C – 700°C for 0.5 – 6 minutes.

Claim 13. (original) The method of claim 7, wherein the substrate includes glass substrate, silicon substrate, or plastic substrate.

Customer No.: 31561
Docket No.: 14150-US-PA
Application No.: 10/711,864

Claim 14. (original) The method of claim 7, wherein substrate includes rigid substrate or flexible substrate.